

**IN THE SPECIFICATION:**

On Page 1, below the title, insert the following:

**--RELATED APPLICATION**

This application is a divisional application of U.S. Patent Application Serial No. 10/061,365, filed February 4, 2002. --

On Page 6 of the specification, change the paragraph starting at line 20 as follows:

--Preferably, the first semiconductor layer is a Si layer, and the second semiconductor layer is a  $\text{Si}_{1-x}\text{Ge}_x\text{C}_y$  layer ( $0 < x < 1$ ,  $0 < y < 1$ ). As a result, excellent characteristics can be obtained using a hetero junction.--

On Page 7 of the specification, change the paragraph starting at line 18 as follows:

--Preferably, the third and fourth semiconductor layers each including a  $\text{Si}_{1-x}\text{Ge}_x\text{C}_y$  layer ( $0 < x < 1$ ,  $0 < y < 1$ ) are formed in the step (b). This enables formation of a semiconductor device including a bipolar transistor having excellent frequency characteristics and a variable capacitor having a large variation range of capacitance.--